Negative Voltage Regulators

MC79L00A Series

The MC79L00A Series negative voltage regulators are inexpensive, easy-to-use devices suitable for numerous applications requiring up to 100 mA. Like the higher powered MC7900 Series negative regulators, this series features thermal shutdown and current limiting, making them remarkably rugged. In most applications, no external components are required for operation.

The MC79L00A devices are useful for on-card regulation or any other application where a regulated negative voltage at a modest current level is needed. These regulators offer substantial advantage over the common resistor/Zener diode approach.

Features

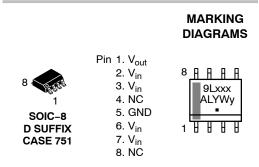
- No External Components Required
- Internal Short Circuit Current Limiting
- Internal Thermal Overload Protection
- Low Cost
- Complementary Positive Regulators Offered (MC78L00 Series)
- Pb-Free Packages are Available

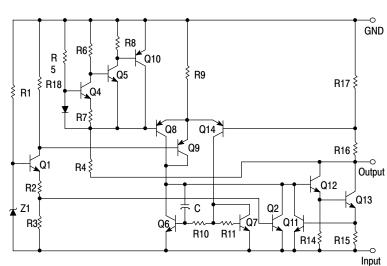


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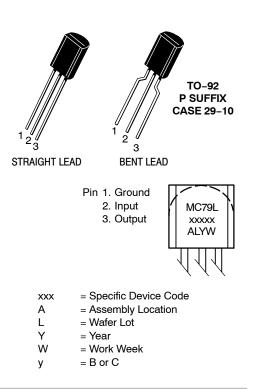
THREE-TERMINAL LOW CURRENT NEGATIVE FIXED VOLTAGE REGULATORS





* Automotive temperature range selections are available with special test conditions and additional tests in 5, 12 and 15 V devices. Contact your local ON Semiconductor sales office for information.

Figure 1. Representative Schematic Diagram



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

MAXIMUM RATINGS (T_A = +25°C, unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage (-5 V) (-12, -15, -18 V) (-24 V)	VI	-30 -35 -40	Vdc
Power Dissipation Case 29 (TO-92 Type) $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case Case 751 (SOIC-8 Type) (Note 1) $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	PD R _{θJA} R _{θJC} PD R _{θJA} R _{θJC}	Internally Limited 160 83 Internally Limited 180 45	₩ °C/W °C/W °C/W °C/W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. SOIC-8 Junction-to-Ambient Thermal Resistance is for minimum recommended pad size. Refer to Figure 9 for Thermal Resistance variation versus pad size.

*This device series contains ESD protection and exceeds the following tests: Human Body Model 2000 V per MIL_STD_883, Method 3015 Machine Model Method 200 V.

ELECTRICAL CHARACTERISTICS (V_I = -10 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		MC79L05AC, AB			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage (T _J = +25°C)	Vo	-4.8	-5.0	-5.2	Vdc
$ \begin{array}{l} \mbox{Input Regulation } (T_J = +25^\circ C) \\ -7.0 \ \mbox{Vdc} \geq V_I \geq -20 \ \ \mbox{Vdc} \\ -8.0 \ \ \mbox{Vdc} \geq V_I \geq -20 \ \ \ \mbox{Vdc} \\ \end{array} $	Reg _{line}			150 100	mV
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \text{ mA} \le I_O \le 100 \text{ mA} \\ 1.0 \text{ mA} \le I_O \le 40 \text{ mA}$	Reg _{load}	-		60 30	mV
Output Voltage $-7.0~Vdc \geq V_l \geq -20~Vdc,~1.0~mA \leq I_O \leq 40~mA$ $V_l = -10~Vdc,~1.0~mA \leq I_O \leq 70~mA$	Vo	-4.75 -4.75		-5.25 -5.25	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	Ι _{ΙΒ}	-		6.0 5.5	mA
Input Bias Current Change $-8.0 \text{ Vdc} \ge V_I \ge -20 \text{ Vdc}$ $1.0 \text{ mA} \le I_O \le 40 \text{ mA}$	Ι _{ΙΒ}	-		1.5 0.1	mA
Output Noise Voltage (T _A = +25°C, 10 Hz \leq f \leq 100 kHz)	V _n	-	40	-	μV
Ripple Rejection (-8.0 \geq V _I \geq -18 Vdc, f = 120 Hz, T _J = +25°C)	RR	41	49	-	dB
Dropout Voltage ($I_O = 40 \text{ mA}, T_J = +25^{\circ}C$)	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -19 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		MC79L12AC, AB			
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	V _O	-11.5	-12	-12.5	Vdc
$ \begin{array}{l} \mbox{Input Regulation } (T_J = +25^\circ C) \\ -14.5 \mbox{ Vdc} \geq V_I \geq -27 \mbox{ Vdc} \\ -16 \mbox{ Vdc} \geq V_I \geq -27 \mbox{ Vdc} \end{array} $	Reg _{line}	-		250 200	mV
Load Regulation $T_J = +25^{\circ}C$, 1.0 mA $\le I_O \le$ 100 mA 1.0 mA $\le I_O \le$ 40 mA	Reg _{load}	-		100 50	mV
$\begin{array}{l} \text{Output Voltage} \\ -14.5 \ \text{Vdc} \geq \text{V}_{I} \geq -27 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq \text{I}_{O} \leq 40 \ \text{mA} \\ \text{V}_{I} = -19 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq \text{I}_{O} \leq 70 \ \text{mA} \end{array}$	V _O	-11.4 -11.4		-12.6 -12.6	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}			6.5 6.0	mA
Input Bias Current Change $-16 \text{ Vdc} \ge V_1 \ge -27 \text{ Vdc}$ $1.0 \text{ mA} \le I_0 \le 40 \text{ mA}$	I _{IB}	-		1.5 0.2	mA
Output Noise Voltage (T _A = +25°C, 10 Hz \leq f \leq 100 kHz)	V _n	-	80	-	μV
Ripple Rejection (-15 \leq V _I \leq -25 Vdc, f = 120 Hz, T _J = +25°C)	RR	37	42	-	dB
Dropout Voltage ($I_0 = 40 \text{ mA}, T_J = +25^{\circ}\text{C}$)	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -23 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC)).

		M	C79L15AC, A	AB	
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage ($T_J = +25^{\circ}C$)	Vo	-14.4	-15	-15.6	Vdc
$ \begin{array}{l} \mbox{Input Regulation } (T_J=+25^\circ C) \\ -17.5 \mbox{ Vdc} \geq V_J \geq -30 \mbox{ Vdc} \\ -20 \mbox{ Vdc} \geq V_J \geq -30 \mbox{ Vdc} \end{array} $	Reg _{line}			300 250	mV
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \text{ mA} \le I_O \le 100 \text{ mA} \\ 1.0 \text{ mA} \le I_O \le 40 \text{ mA}$	Reg _{load}	-	- -	150 75	mV
Output Voltage $-17.5 \text{ Vdc} \ge V_I \ge -\text{Vdc}, 1.0 \text{ mA} \le I_O \le 40 \text{ mA}$ $V_I = -23 \text{ Vdc}, 1.0 \text{ mA} \le I_O \le 70 \text{ mA}$	Vo	-14.25 -14.25		-15.75 -15.75	Vdc
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}			6.5 6.0	mA
Input Bias Current Change -20 Vdc \ge V _I \ge -30 Vdc 1.0 mA \le I _O \le 40 mA	Δl _{IB}	-		1.5 0.1	mA
Output Noise Voltage (T _A = +25°C, 10 Hz \leq f \leq 100 kHz)	V _N	-	90	-	μV
Ripple Rejection (–18.5 \leq V _I \leq –28.5 Vdc, f = 120 Hz)	RR	34	39	-	dB
Dropout Voltage I _O = 40 mA, T_J = +25°C	V _I -V _O	-	1.7	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V _I = -27 V, I _O = 40 mA, C _I = 0.33 μ F, C _O = 0.1 μ F, -40°C < T _J +125°C (for MC79LXXAB),
0° C < T _J < +125^{\circ}C (for MC79LXXAC), unless otherwise noted).

			MC79L18AC	;	
Characteristics	Symbol	Min	Тур	Max	Unit
Output Voltage (T _J = +25°C)	Vo	-17.3	-18	-18.7	Vdo
$\begin{array}{l} \mbox{Input Regulation } (T_J = +25^\circ C) \\ -20.7 \mbox{ Vdc } \geq V_I \geq -33 \mbox{ Vdc} \\ -21.4 \mbox{ Vdc } \geq V_I \geq -33 \mbox{ Vdc} \\ -22 \mbox{ Vdc } \geq V_I \geq -33 \mbox{ Vdc} \\ -21 \mbox{ Vdc } \geq V_I \geq -33 \mbox{ Vdc} \\ \end{array}$	Reg _{line}	- - - -	- - - -	325 _ _ 275	mV
Load Regulation $T_J = +25^{\circ}C$, 1.0 mA $\le I_O \le 100$ mA 1.0 mA $\le I_O \le 40$ mA	Reg _{load}	-		170 85	mV
$\begin{array}{l} \text{Output Voltage} \\ -20.7 \ \text{Vdc} \geq V_l \geq -33 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq I_O \leq 40 \ \text{mA} \\ -21.4 \ \text{Vdc} \geq V_l \geq -33 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq I_O \leq 40 \ \text{mA} \\ V_l = -27 \ \text{Vdc}, \ 1.0 \ \text{mA} \leq I_O \leq 70 \ \text{mA} \end{array}$	Vo	-17.1 - -17.1	- - -	-18.9 - -18.9	Vdo
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	I _{IB}	- -		6.5 6.0	mA
$ \begin{array}{l} \mbox{Input Bias Current Change} \\ -21 \mbox{ Vdc} \geq V_l \geq -33 \mbox{ Vdc} \\ -27 \mbox{ Vdc} \geq V_l \geq -33 \mbox{ Vdc} \\ 1.0 \mbox{ mA} \leq I_O \leq 40 \mbox{ mA} \end{array} $	I _{IB}	- - -	- - -	1.5 	mA
Output Noise Voltage (T _A = +25°C, 10 Hz \leq f \leq 100 kHz)	Vn	_	150	-	μV
Ripple Rejection (–23 \leq V _I \leq –33 Vdc, f = 120 Hz, T _J = +25°C)	RR	33	48	-	dB
Dropout Voltage I _O = 40 mA, T _J = +25°C	V _I -V _{OI}	_	1.7	_	Vdd

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (V_I = -33 V, I_O = 40 mA, C_I = 0.33 μ F, C_O = 0.1 μ F, -40°C < T_J +125°C (for MC79LXXAB), 0°C < T_J < +125°C (for MC79LXXAC), unless otherwise noted).

		MC79L24AC				
Characteristics	Symbol	Min	Тур	Max	Unit	
Output Voltage (T _J = $+25^{\circ}$ C)	Vo	-23	-24	-25	Vdc	
$\begin{array}{l} \mbox{Input Regulation } (T_J = +25^\circ C) \\ -27 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ Vdc} \\ -27.5 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ Vdc} \\ -28 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ Vdc} \end{array}$	Reg _{line}			350 	mV	
Load Regulation $T_J = +25^{\circ}C, \ 1.0 \text{ mA} \le I_O \le 100 \text{ mA}$ 1.0 mA $\le I_O \le 40 \text{ mA}$	Reg _{load}			200 100	mV	
$ \begin{array}{l} \mbox{Output Voltage} \\ -27 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ V}, \mbox{ 1.0 mA} \leq I_O \leq 40 \mbox{ mA} \\ -28 \mbox{ Vdc} \geq V_l \geq -38 \mbox{ Vdc}, \mbox{ 1.0 mA} \leq I_O \leq 40 \mbox{ mA} \\ \mbox{ V}_l = -33 \mbox{ Vdc}, \mbox{ 1.0 mA} \leq I_O \leq 70 \mbox{ mA} \end{array} $	Vo	-22.8 - -22.8	- - -	-25.2 - -25.2	Vdc	
Input Bias Current $(T_J = +25^{\circ}C)$ $(T_J = +125^{\circ}C)$	Ι _{ΙΒ}	-		6.5 6.0	mA	
Input Bias Current Change -28 Vdc \ge V _I \ge -38 Vdc 1.0 mA \le I _O \le 40 mA	Δl _{IB}			1.5 0.1	mA	
Output Noise Voltage (T _A = +25°C, 10 Hz \leq f \leq 100 kHz)	Vn	-	200	-	μV	
Ripple Rejection (-29 \leq V _I \leq -35 Vdc, f = 120 Hz, T _J = +25°C)	RR	31	47	-	dB	
Dropout Voltage I _O = 40 mA, T_J = +25°C	V _I -V _O	-	1.7	-	Vdc	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

APPLICATIONS INFORMATION

Design Considerations

The MC79L00A Series of fixed voltage regulators are designed with Thermal Overload Protections that shuts down the circuit when subjected to an excessive power overload condition, Internal Short Circuit Protection that limits the maximum current the circuit will pass.

In many low current applications, compensation capacitors are not required. However, it is recommended that the regulator input be bypassed with a capacitor if the regulator is connected to the power supply filter with long wire length, or if the output load capacitance is large. An input bypass capacitor should be selected to provide good

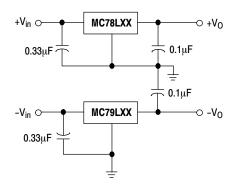
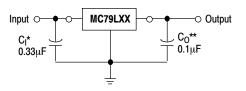


Figure 2. Positive and Negative Regulator

high-frequency characteristics to insure stable operation under all load conditions. A 0.33 μ F or larger tantalum, mylar, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with the shortest possible leads directly across the regulator's input terminals. Normally good construction techniques should be used to minimize ground loops and lead resistance drops since the regulator has no external sense lead. Bypassing the output is also recommended.



A common ground is required between the input and the output voltages. The input voltage must remain typically 2.0 V above the output voltage even during the low point on the ripple voltage.

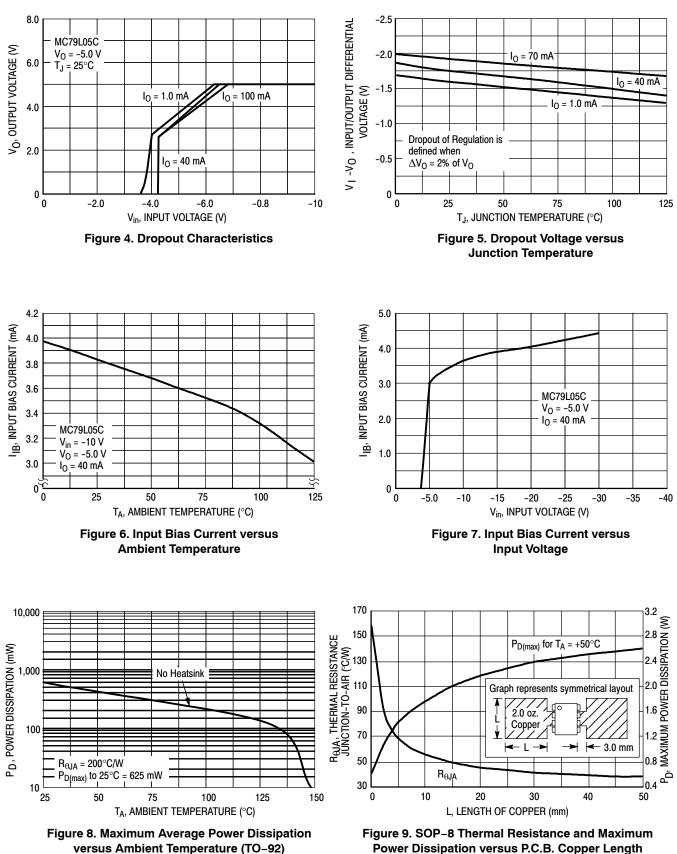
* C_I is required if regulator is located an appreciable distance from the power supply filter

** CO improves stability and transient response.

Figure 3. Standard Application

TYPICAL CHARACTERISTICS

(T_A = +25°C, unless otherwise noted.)



ORDERING INFORMATION

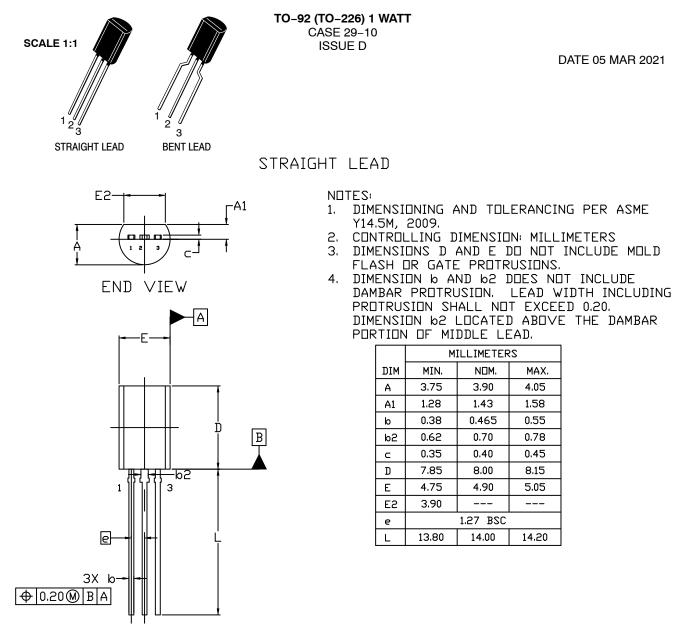
Device	Nominal Voltage	Operating Temperature Range	Package	Shipping [†]
MC79L05ABDG	–5.0 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ABDR2G		-	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ABPG		-	TO–92 (Pb–Free)	2000 Units / Bag
MC79L05ABPRAG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L05ACDG		$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L05ACDR2G		-	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L05ACPG		-	TO–92 (Pb–Free)	2000 Units / Bag
MC79L05ACPRAG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L05ACPRMG		-	TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L05ACPRPG			TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L12ABDG	–12 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ABDR2G		-	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ABPG		-	TO–92 (Pb–Free)	2000 Units / Bag
MC79L12ABPRAG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L12ACDG	–12 V	$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L12ACDR2G		-	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L12ACPG		-	TO–92 (Pb–Free)	2000 Units / Bag
MC79L12ACPRAG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L12ACPRPG		-	TO–92 (Pb–Free)	2000 / Tape & Ammo Box

ORDERING INFORMATION (continued)

Device	Nominal Voltage	Operating Temperature Range	Package	Shipping [†]
MC79L15ABDG	–15 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ABDR2G		-	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ABPG		-	TO-92 (Pb-Free)	2000 Units / Bag
MC79L15ABPRPG		-	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L15ACDG		$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC79L15ACDR2G			SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC79L15ACPG		-	TO-92 (Pb-Free)	2000 Units / Bag
MC79L15ACPRAG		-	TO-92 (Pb-Free)	2000 / Tape & Reel
MC79L15ACPREG		-	TO–92 (Pb–Free)	2000 / Tape & Reel
MC79L15ACPRPG		-	TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L18ABPRPG	–18 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MC79L18ACPG		TJ = 0° to +125°C	TO-92 (Pb-Free)	2000 Units / Bag
MC79L24ABPG	–24 V	$TJ = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	TO–92 (Pb–Free)	2000 Units / Bag
MC79L24ACPG		$TJ = 0^{\circ} \text{ to } +125^{\circ}\text{C}$	TO–92 (Pb–Free)	2000 Units / Bag
MC79L24ACPRMG			TO–92 (Pb–Free)	2000 / Tape & Ammo Box
MC79L24ACPRPG			TO–92 (Pb–Free)	2000 / Tape & Ammo Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<u>Onsemi</u>,



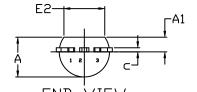
TOP VIEW

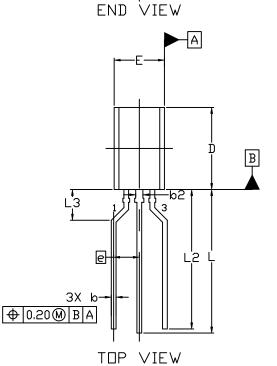
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DATE 05 MAR 2021

FORMED LEAD





NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS				
DIM	MIN.	NDM.	MAX.		
Α	3.75	3.90	4.05		
A1	1.28	1.43	1.58		
α	0.38	0.465	0.55		
b2	0.62	0.70	0.78		
с	0.35	0.40	0.45		
D	7.85	8.00	8.15		
E	4.75	4.90	5.05		
E5	3.90				
e	2.50 BSC				
L	13.80	14.00	14.20		
L2	13.20	13.60	14.00		
L3		3.00 REF			

STYLES AND MARKING ON PAGE 3

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TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

STYLE 5:

PIN 1. DRAIN

	EMITTER BASE COLLECTOR
	GATE SOURCE & SUBSTRATE DRAIN
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
	V _{CC} GROUND 2 OUTPUT

STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2 STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT STYLE 32 PIN 1. BASE 2. COLLECTOR

3 EMITTER

2.	ANODE ANODE CATHODE
2.	DRAIN Gate Source & Substrate
2.	ANODE 1 GATE CATHODE 2
2.	ANODE CATHODE NOT CONNECTED
2.	GATE SOURCE DRAIN
2.	CATHODE ANODE GATE
2.	: RETURN INPUT OUTPUT

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 9: PIN 1. BASE 1 EMITTER 2. 3. BASE 2 STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE

STYLE 34:

PIN 1. INPUT

2. GROUND

3. LOGIC

2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

GENERIC **MARKING DIAGRAM***

XXXXX XXXXX ALYW= .

XXXX = Specific Device Code

- А = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
 - = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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7.

8

COLLECTOR, #1

COLLECTOR, #1

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